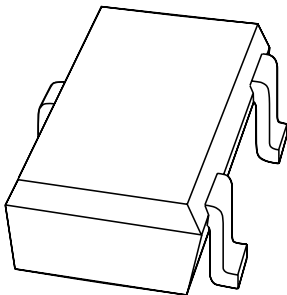


DATA SHEET



BC817W

NPN general purpose transistor

Product specification
Supersedes data of 1997 Mar 05

1999 Apr 15

NPN general purpose transistor

BC817W

FEATURES

- High current (max. 500 mA)
- Low voltage (max. 45 V).

APPLICATIONS

- General purpose switching and amplification.

DESCRIPTION

NPN transistor in a SOT323 plastic package.
PNP complement: BC807W.

MARKING

TYPE NUMBER	MARKING CODE ⁽¹⁾	TYPE NUMBER	MARKING CODE ⁽¹⁾
BC817W	6D*	BC818W	6H*
BC817-16W	6A*	BC818-16W	6E*
BC817-25W	6B*	BC818-25W	6F*
BC817-40W	6C*	BC818-40W	6G*

Note

- * = - : Made in Hong Kong.
* = t : Made in Malaysia.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector

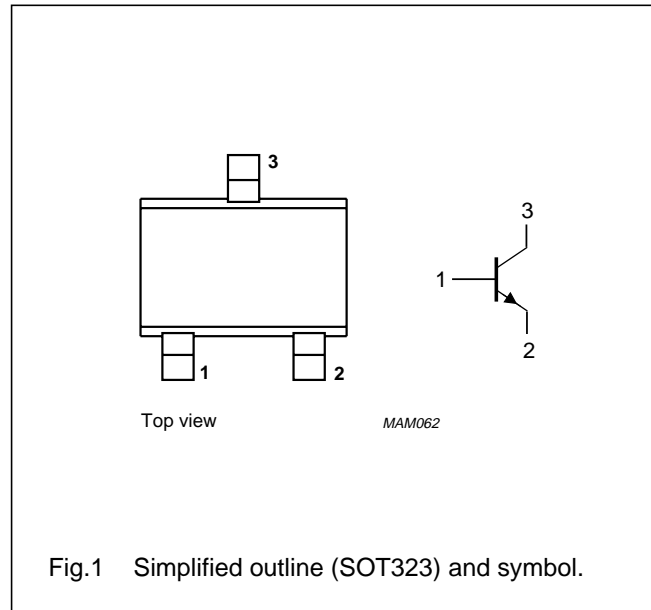


Fig.1 Simplified outline (SOT323) and symbol.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	–	50	V
V _{CEO}	collector-emitter voltage	open base; I _C = 10 mA	–	45	V
V _{EBO}	emitter-base voltage	open collector	–	5	V
I _C	collector current (DC)		–	500	mA
I _{CM}	peak collector current		–	1	A
I _{BM}	peak base current		–	200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	–	200	mW
T _{stg}	storage temperature		–65	+150	°C
T _j	junction temperature		–	150	°C
T _{amb}	operating ambient temperature		–65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

NPN general purpose transistor

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	625	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

$T_{amb} = 25\text{ °C}$ unless otherwise specified.

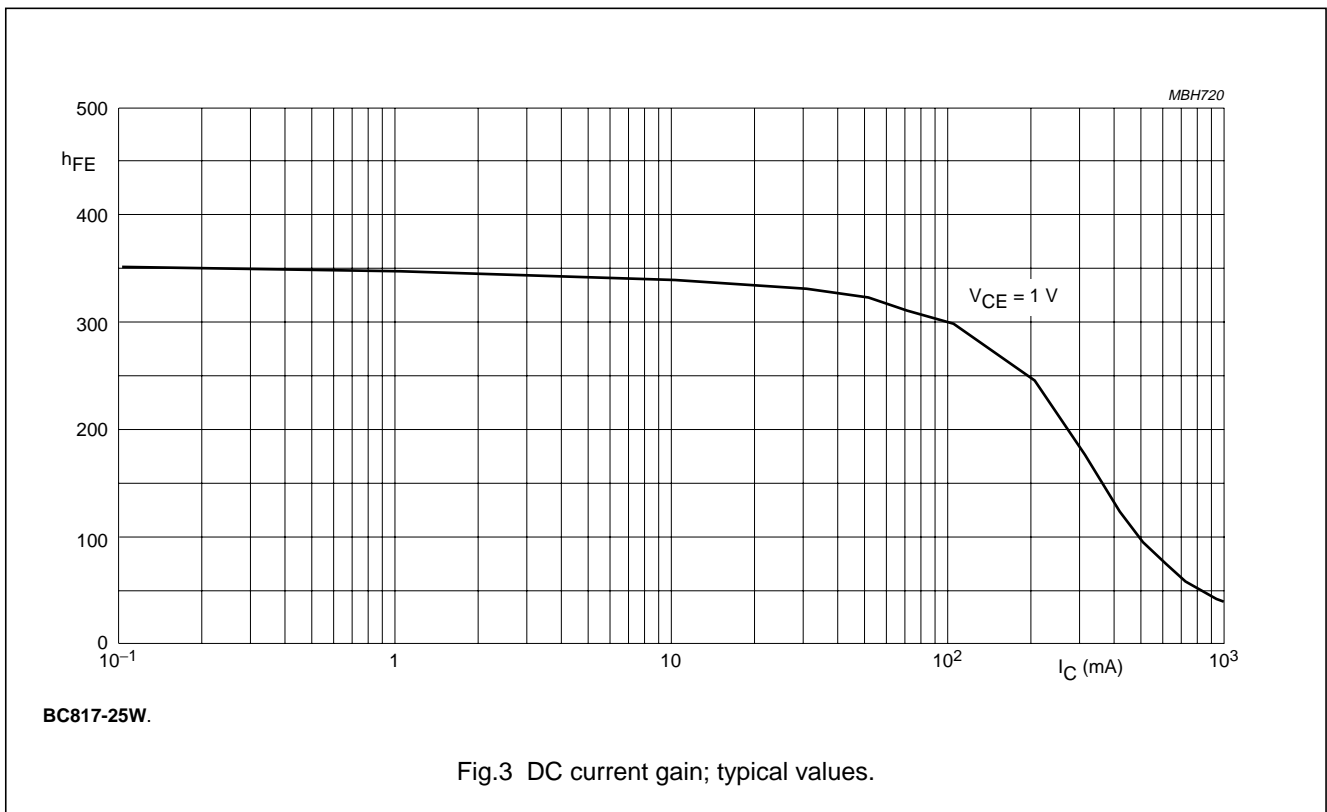
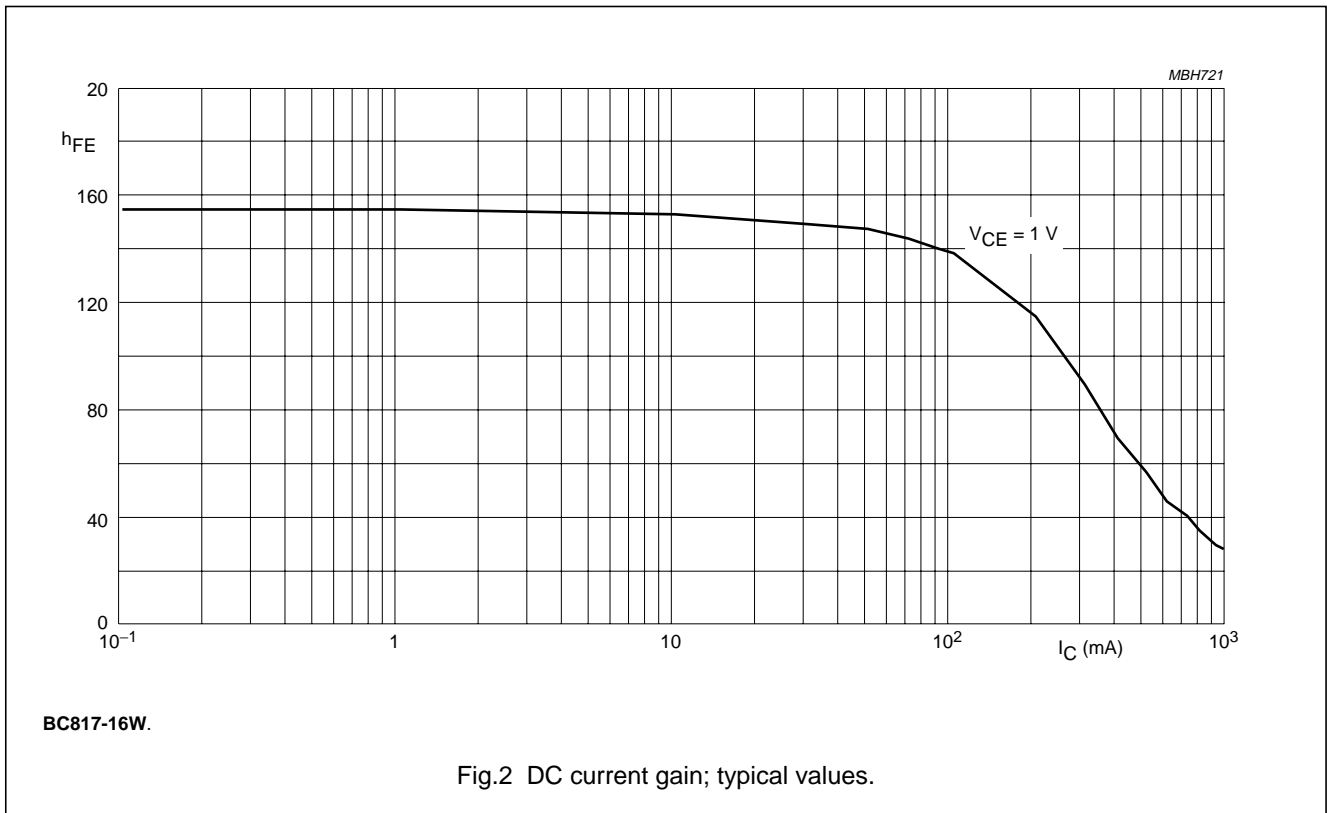
SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT	
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = 20\text{ V}$	–	100	nA	
		$I_E = 0; V_{CB} = 20\text{ V}; T_j = 150\text{ °C}$	–	5	μA	
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = 5\text{ V}$	–	100	nA	
h_{FE}	DC current gain	$I_C = 100\text{ mA}; V_{CE} = 1\text{ V};$ note 1; see Figs 2, 3 and 4				
			BC817W	100	600	
			BC817-16W	100	250	
			BC817-25W	160	400	
	BC817-40W	250	600			
	DC current gain	$I_C = 500\text{ mA}; V_{CE} = 1\text{ V};$ note 1	40	–		
V_{CEsat}	collector-emitter saturation voltage	$I_C = 500\text{ mA}; I_B = 50\text{ mA};$ note 1	–	700	mV	
V_{BE}	base-emitter voltage	$I_C = 500\text{ mA}; V_{CE} = 1\text{ V};$ note 1	–	1.2	mV	
C_c	collector capacitance	$I_E = i_e = 0; V_{CB} = 10\text{ V}; f = 1\text{ MHz}$	–	5	pF	
f_T	transition frequency	$I_C = 10\text{ mA}; V_{CE} = 5\text{ V}; f = 100\text{ MHz}$	100	–	MHz	

Note

1. Pulse test: $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02.$

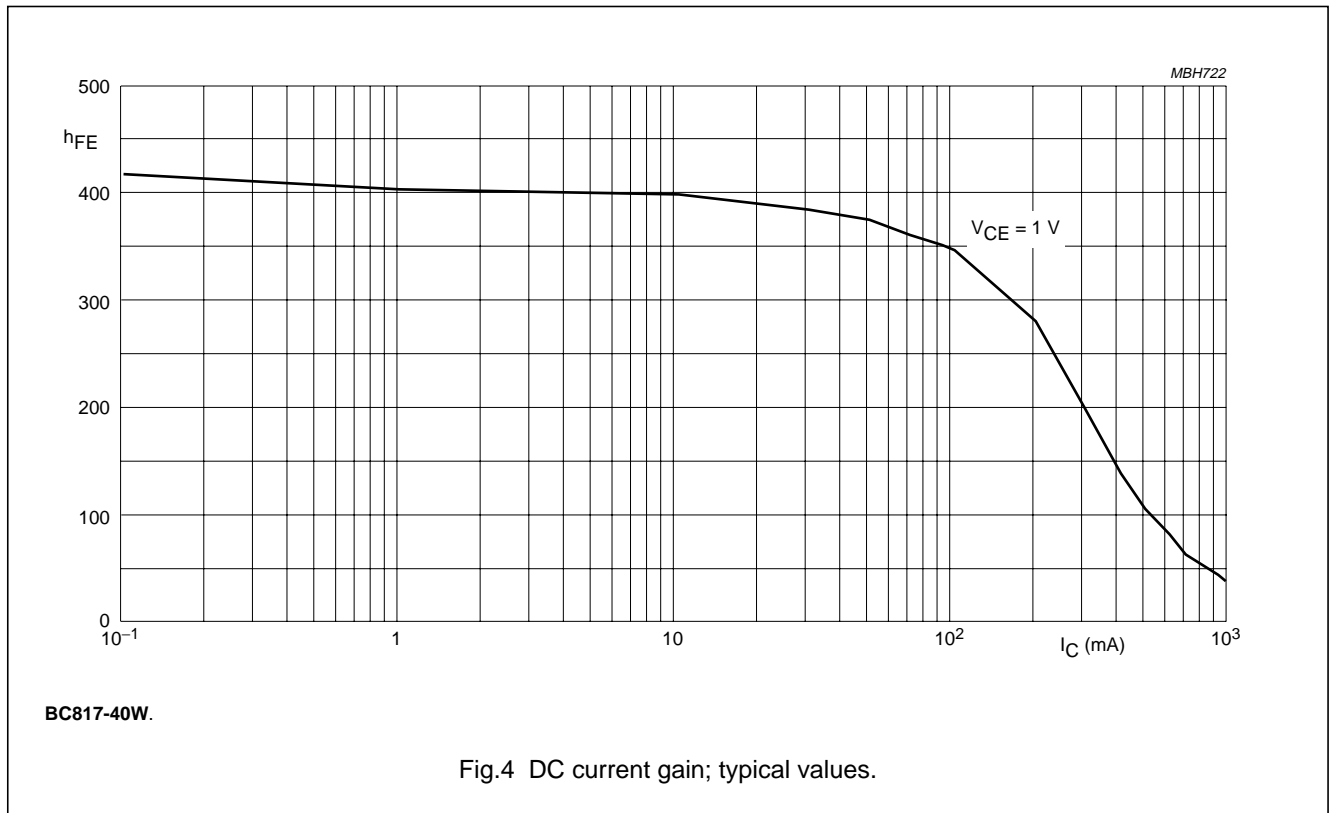
NPN general purpose transistor

BC817W



NPN general purpose transistor

BC817W



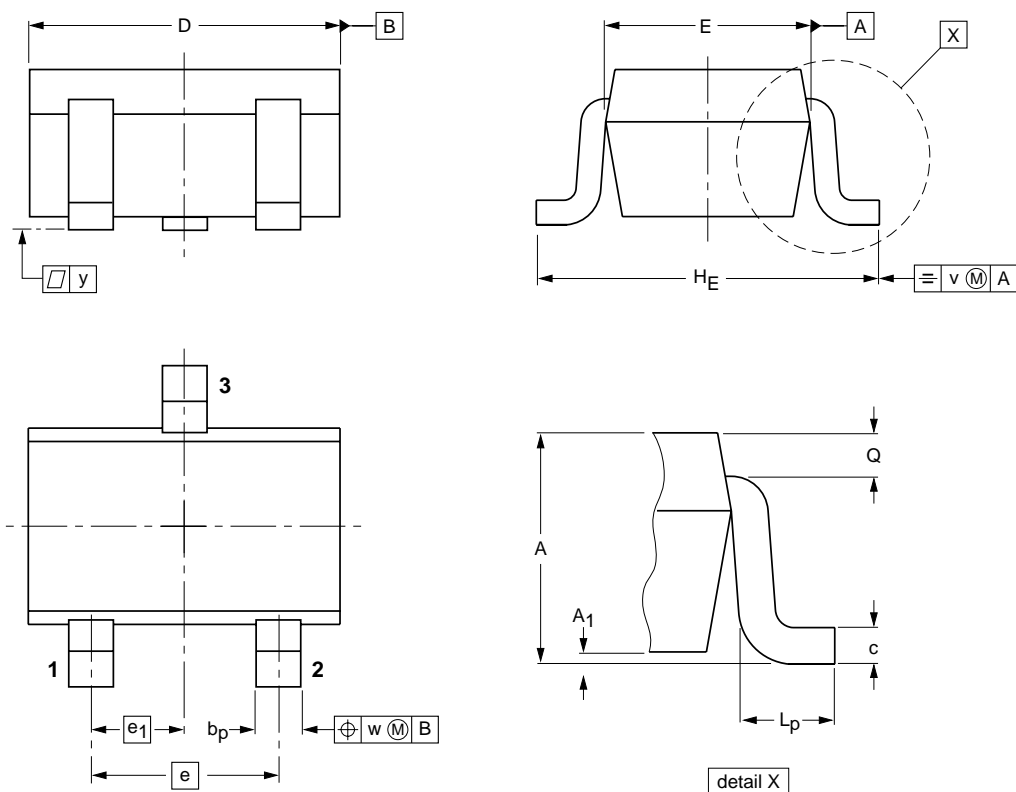
NPN general purpose transistor

BC817W

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT323



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.8	0.1	0.4 0.3	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.23 0.13	0.2	0.2

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT323			SC-70			97-02-28

NPN general purpose transistor

BC817W

DEFINITIONS

Data Sheet Status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

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